

2SB1417, 2SB1417A

Silicon PNP epitaxial planar type

For power amplification

Complementary to 2SD2137 and 2SD2137A

■ Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Allowing automatic insertion with radial tapering

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Collector to base voltage	2SB1417	V_{CBO}	-60	V
	2SB1417A		-80	
Collector to emitter voltage	2SB1417	V_{CEO}	-60	V
	2SB1417A		-80	
Emitter to base voltage		V_{EBO}	-6	V
Peak collector current		I_{CP}	-5	A
Collector current		I_C	-3	A
Collector power dissipation	$T_C = 25^{\circ}\text{C}$	P_C	15	W
	$T_a = 25^{\circ}\text{C}$		2.0	
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^{\circ}\text{C}$

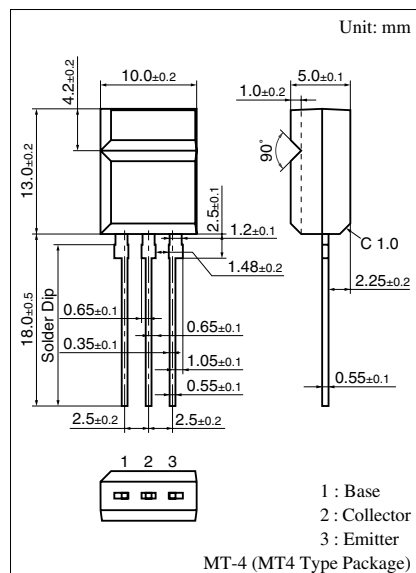
■ Electrical Characteristics $T_C = 25^\circ\text{C}$

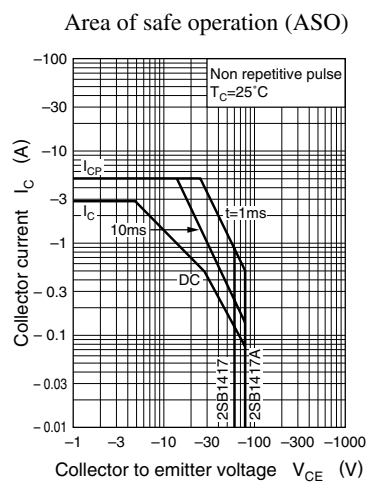
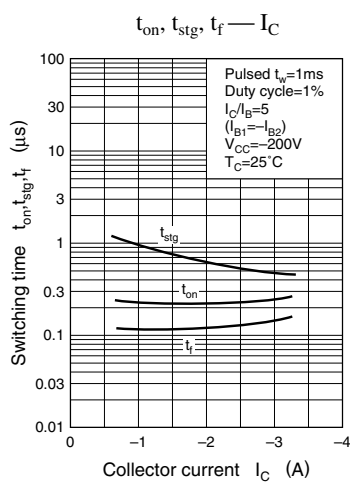
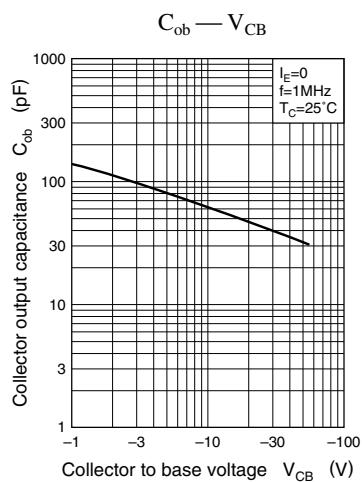
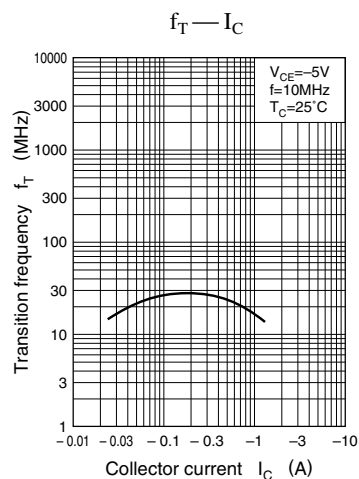
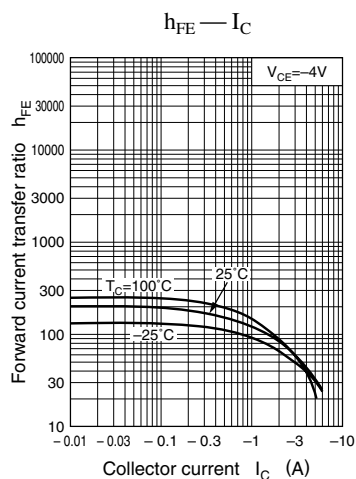
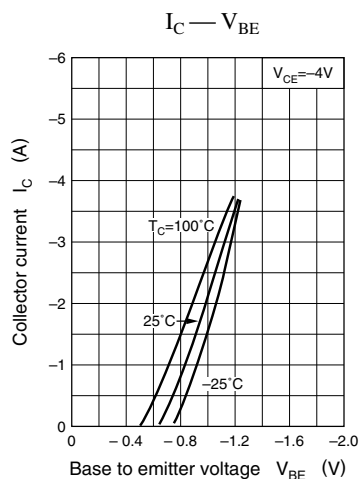
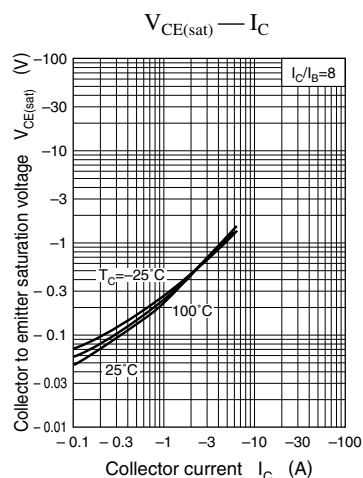
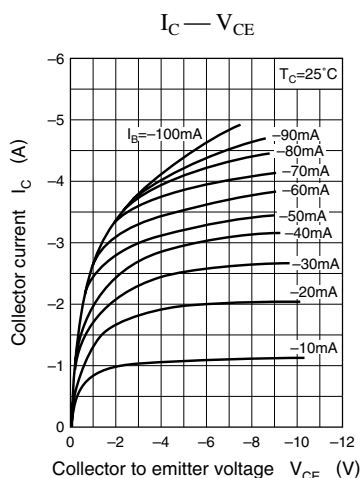
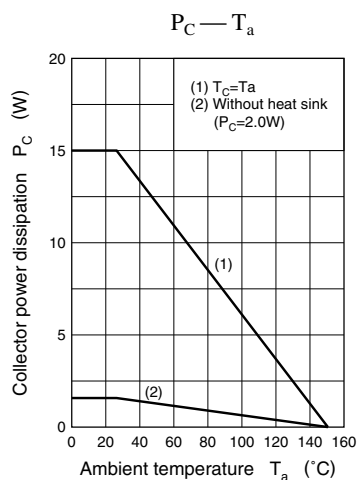
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	2SB1417 2SB1417A	I_{CES} $V_{CE} = -60\text{ V}, V_{BE} = 0$			-100	μA
					-100	
Collector cutoff current	2SB1417 2SB1417A	I_{CEO} $V_{CE} = -30\text{ V}, I_B = 0$			-100	μA
					-100	
Emitter cutoff current	I_{EBO}	$V_{EB} = -6\text{ V}, I_C = 0$			-100	μA
Collector to emitter voltage	2SB1417 2SB1417A	V_{CEO} $I_C = -30\text{ mA}, I_B = 0$	-60			V
			-80			
Forward current transfer ratio	h_{FE1}^* h_{FE2}	$V_{CE} = -4\text{ V}, I_C = -1\text{ A}$ $V_{CE} = -4\text{ V}, I_C = -3\text{ A}$	70		250	
			10			
Base to emitter voltage	V_{BE}	$V_{CE} = -4\text{ V}, I_C = -3\text{ A}$			-1.8	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -3\text{ A}, I_B = -0.375\text{ A}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -0.2\text{ A}, f = 10\text{ MHz}$		30		MHz
Turn-on time	t_{on}	$I_C = -1\text{ A}, I_{B1} = -0.1\text{ A}, I_{B2} = 0.1\text{ A}, V_{CC} = -50\text{ V}$		0.3		μs
Storage time	t_{stg}			1.0		μs
Fall time	t_f			0.2		μs

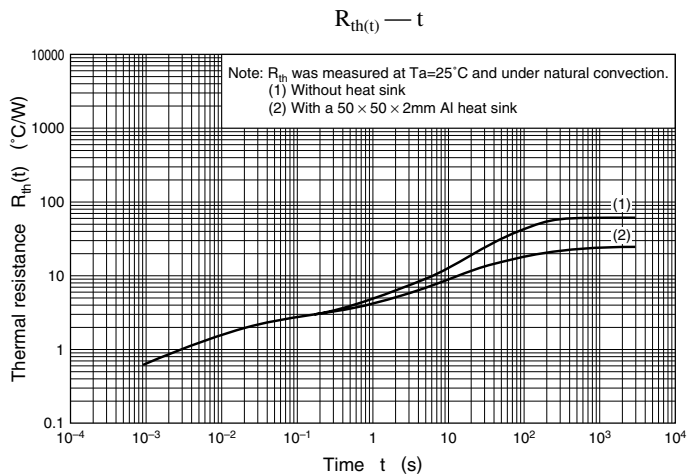
Note) *: Rank classification

Rank	Q	P
h_{FE1}	70 to 150	120 to 250

Ordering can be made by the common rank (PQ rank $h_{FE1} = 70$ to 250) in the rank classification.







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